L Number	Hits	Search Text	DB	Time stamp
1	2	("6222225").PN.	USPAT;	2004/07/20 11:08
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
2	5324	257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:08
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
3	4472	438/201,211,216,241,257,258,260-266,591,593.ccls.	USPAT;	2004/07/20 11:10
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
4	9114	257/239,261,298,315-326.ccls.	USPĀT;	2004/07/20 11:10
·		438/201,211,216,241,257,258,260-266,591,593.ccls.	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM TDB	
5	1987	(257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:43
	1,0,	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)	ЕРО; ЛРО;	
		Total Marian, y	DERWENT;	
			IBM TDB	
6	186	((257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:18
	100	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЛРО;	
		dielectric)) with (second near gate near (insulat\$3 oxide dielectric)))	DERWENT;	
		diciocatio)) with (cocona near gate near (meanage since are are and)))	IBM_TDB	
7	32	(((257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:14
	32	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЈРО;	
		dielectric)) with (second near gate near (insulat\$3 oxide dielectric))))	DERWENT;	
		and ((first near thick\$4) with (second near thick\$4))	IBM_TDB	
8	68	((257/239,261,298,315-326.ccls.	USPAT;	2004/07/20 11:38
		438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	
		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЈРО;	
		dielectric)) with (second near gate near (insulat\$3 oxide dielectric)) with	DERWENT;	
		thick\$4)	IBM_TDB	
9	8	((257/239,261,298,315-326.ccls.	USPĀT;	2004/07/20 11:43
	_	438/201,211,216,241,257,258,260-266,591,593.ccls.) and (non near	US-PGPUB;	1
İ		volatile near memory)) and ((first near gate near (insulat\$3 oxide	ЕРО; ЈРО;	
		dielectric) near thick\$4) with (second near gate near (insulat\$3 oxide	DERWENT,	
		dielectric) near thick\$4))	IBM_TDB	
10	349594	257/\$.ccls. 438/\$.ccls.	USPĀT;	2004/07/20 11:43
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
	i .	(257/\$.ccls. 438/\$.ccls.) and (non near volatile near memory)	USPAT;	2004/07/20 11:49
11	5004			1
11	5004		OS-PGPUB:	
11	5004		US-PGPUB; EPO; JPO;	
11	5004		EPO; JPO; DERWENT;	
11	5004		EPO, JPO, DERWENT,	
		((257/\$.ccls, 438/\$.ccls.) and (non near volatile near memory)) and	EPO; JPO; DERWENT; IBM_TDB	2004/07/20 11:49
11	5004	((257/\$.ccls. 438/\$.ccls.) and (non near volatile near memory)) and ((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/07/20 11:49
		((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/07/20 11:49
			EPO, JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO, JPO;	2004/07/20 11:49
		((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/07/20 11:49

14	60231	non near volatile near memory	USPAT;	2004/07/20 11:49
ļ			US-PGPUB;	
			ЕРО; ЛРО;	
	1		DERWENT;	
			IBM_TDB	
15	16	(non near volatile near memory) and ((first near gate near (insulat\$3	USPAT;	2004/07/20 11:55
		oxide dielectric) near thick\$4) with (second near gate near (insulat\$3	US-PGPUB;	
		oxide dielectric) near thick\$4))	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
16	44	((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	USPAT;	2004/07/20 11:52
		(greater bigger larger) with (second near gate near (insulat\$3 oxide	US-PGPUB;	
		dielectric) near thick\$4))	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
17	179	((first near gate near (insulat\$3 oxide dielectric) near thick\$4) with	USPAT;	2004/07/20 11:55
		(second near gate near (insulat\$3 oxide dielectric) near thick\$4))	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	